CAD for MEMS

# Computer-Aided Design for Micro-Electro-Mechanical Systems Eigenvalues, Energy Losses, and Dick Tracy Watches

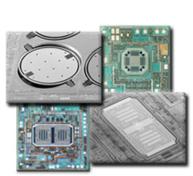
D. Bindel

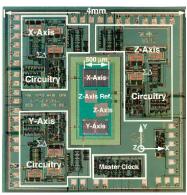
Computer Science Division Department of EECS University of California, Berkeley

Bay Area Scientific Computing Day, 4 Mar 2006

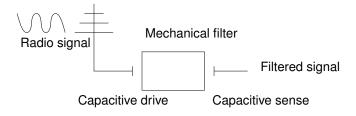


#### What are MEMS?





#### Micromechanical Filters



- Mechanical high-frequency (high MHz-GHz) filter
  - Your cell phone is mechanical!
  - New MEMS filters can be integrated with circuitry
    - ⇒ smaller and lower power

### **Ultimate Success**

"Calling Dick Tracy!"



## **Designing Transfer Functions**

CAD for MEMS

Time domain:

$$Mu'' + Cu' + Ku = b\phi(t)$$
$$y(t) = \rho^{T} u$$

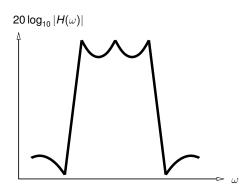
Frequency domain:

$$-\omega^{2}M\hat{u} + i\omega C\hat{u} + K\hat{u} = b\hat{\phi}(\omega)$$
$$\hat{y}(\omega) = p^{T}\hat{u}$$

Transfer function:

$$H(\omega) = \rho^{T} (-\omega^{2} M + i\omega C + K)^{-1} b$$
  
$$\hat{y}(\omega) = H(\omega) \hat{\phi}(\omega)$$

#### Narrowband Filter Needs



- Want "sharp" poles for narrowband filters
- Want to minimize damping

Designers want high quality of resonance (Q)

Dimensionless damping in a one-dof system

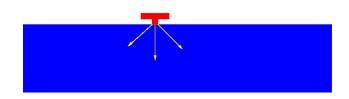
$$\frac{d^2u}{dt^2} + Q^{-1}\frac{du}{dt} + u = F(t)$$

• For a resonant mode with frequency  $\omega \in \mathbb{C}$ :

$$Q := \frac{|\omega|}{2\operatorname{Im}(\omega)} = \frac{\operatorname{Stored energy}}{\operatorname{Energy loss per radian}}$$

## **Damping Mechanisms**

CAD for MEMS



#### Possible loss mechanisms:

- Fluid damping
- Material losses
- Thermoelastic damping
- Anchor loss

Model substrate as semi-infinite with a

Perfectly Matched Layer (PML).



## Perfectly Matched Layers

- Complex coordinate transformation
- Generates a "perfectly matched" absorbing layer
- Idea works with general linear wave equations
  - Electromagnetics (Berengér, 1994)
  - Quantum mechanics exterior complex scaling (Simon, 1979)
  - Elasticity in standard finite element framework (Basu and Chopra, 2003)

- Domain:  $x \in [0, \infty)$
- Governing eq:

$$\frac{\partial^2 u}{\partial x^2} - \frac{1}{c^2} \frac{\partial^2 u}{\partial t^2} = 0$$

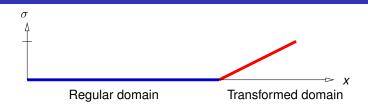
Fourier transform:

$$\frac{d^2\hat{u}}{dx^2} + k^2\hat{u} = 0$$

Solution:

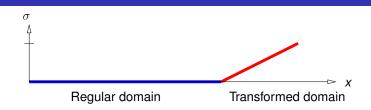
$$\hat{u} = c_{\text{out}} e^{-ikx} + c_{\text{in}} e^{ikx}$$

## Model with Perfectly Matched Layer



$$rac{d ilde{x}}{dx} = \lambda(x) ext{ where } \lambda(s) = 1 - i\sigma(s)$$
 
$$rac{d^2\hat{u}}{d ilde{x}^2} + k^2\hat{u} = 0$$
 
$$\hat{u} = c_{ ext{out}}e^{-ik ilde{x}} + c_{ ext{in}}e^{ik ilde{x}}$$

## Model with Perfectly Matched Layer



$$\frac{d\tilde{x}}{dx} = \lambda(x) \text{ where } \lambda(s) = 1 - i\sigma(s),$$

$$\frac{1}{\lambda} \frac{d}{dx} \left( \frac{1}{\lambda} \frac{d\hat{u}}{dx} \right) + k^2 \hat{u} = 0$$

$$\hat{u} = c_{\text{out}}e^{-ikx-k\Sigma(x)} + c_{\text{in}}e^{ikx+k\Sigma(x)}$$

$$\Sigma(x) = \int_{0}^{x} \sigma(s) \, ds$$

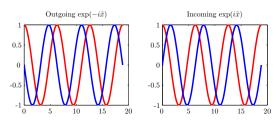
## Model with Perfectly Matched Layer

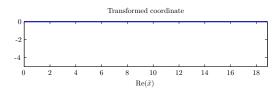
CAD for MEMS

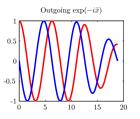


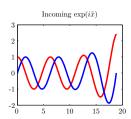
If solution clamped at x = L then

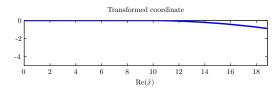
$$rac{m{c}_{
m in}}{m{c}_{
m out}} = m{O}(m{e}^{-k\gamma}) ext{ where } \gamma = m{\Sigma}(m{L}) = \int_0^{m{L}} \sigma(m{s}) \, dm{s}$$

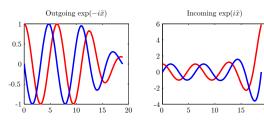


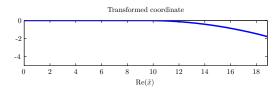


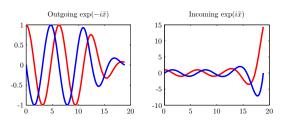


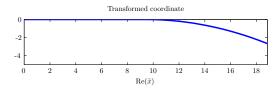


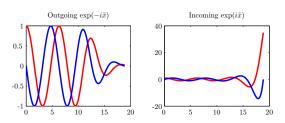


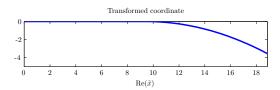


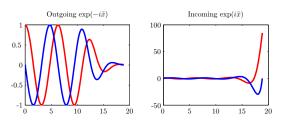


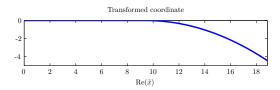






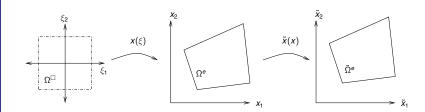






## Finite Element Implementation

CAD for MEMS



Combine PML and isoparametric mappings

$$\mathbf{k}^{e} = \int_{\Omega^{\square}} \tilde{\mathbf{B}}^{T} \mathbf{D} \tilde{\mathbf{B}} \tilde{J} d\Omega^{\square}$$
$$\mathbf{m}^{e} = \int_{\Omega^{\square}} \rho \mathbf{N}^{T} \mathbf{N} \tilde{J} d\Omega^{\square}$$

Matrices are complex symmetric

## Eigenvalues and Model Reduction

CAD for MEMS

Want to know about the transfer function  $H(\omega)$ :

$$H(\omega) = p^{T}(K - \omega^{2}M)^{-1}b$$

Can either

- Locate poles of *H* (eigenvalues of (*K*, *M*))
- Plot *H* in a frequency range (Bode plot)

Usual tactic: subspace projection

- Build an Arnoldi basis V
- Compute with much smaller V\*KV and V\*MV

Can we do better?



- Variational form for complex symmetric eigenproblems:
  - Hermitian (Rayleigh quotient):

$$\rho(\mathbf{v}) = \frac{\mathbf{v}^* \mathbf{K} \mathbf{v}}{\mathbf{v}^* \mathbf{M} \mathbf{v}}$$

• Complex symmetric (modified Rayleigh quotient):

$$\theta(v) = \frac{v^T K v}{v^T M v}$$

- Key: relation between left and right eigenvectors.

#### **Accurate Model Reduction**

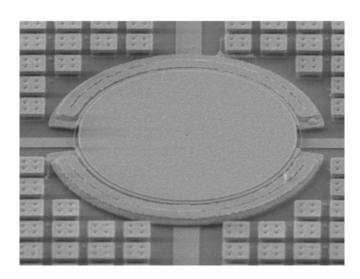
CAD for MEMS

Build new projection basis from V:

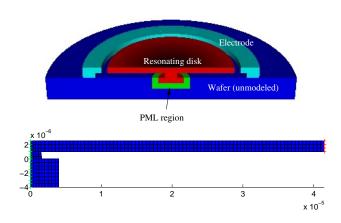
$$W = \operatorname{orth}[\operatorname{Re}(V), \operatorname{Im}(V)]$$

- span(W) contains both  $\mathcal{K}_n$  and  $\bar{\mathcal{K}}_n$   $\Longrightarrow$  double digits correct vs. projection with V
- W is a real-valued basis
  - ⇒ projected system is complex symmetric

#### **Disk Resonator Simulations**



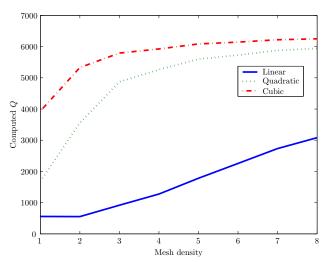
#### Disk Resonator Mesh



- Axisymmetric model with bicubic mesh
- About 10K nodal points in converged calculation

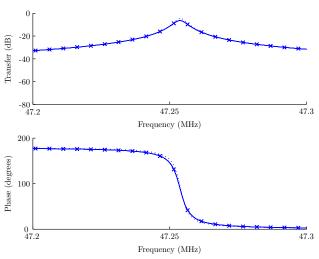


## Mesh Convergence



Cubic elements converge with reasonable mesh density

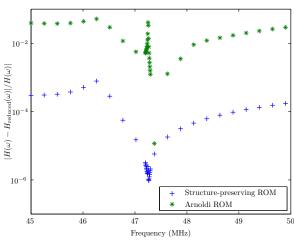
## Model Reduction Accuracy



Results from ROM (solid and dotted lines) nearly indistinguishable from full model (crosses)

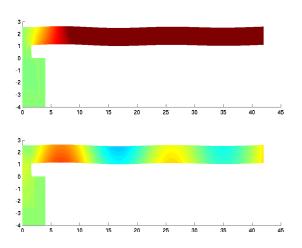
## **Model Reduction Accuracy**

CAD for MEMS

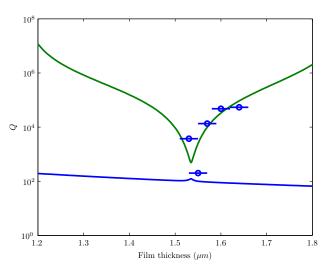


Preserve structure ⇒ get twice the correct digits

## Response of the Disk Resonator

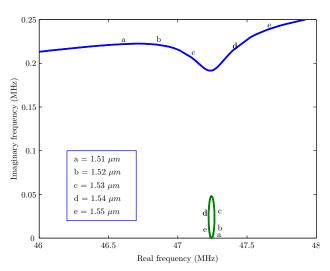


## Variation in Quality of Resonance



Simulation and lab measurements vs. disk thickness

## Explanation of Q Variation



Interaction of two nearby eigenmodes

#### Conclusions

- RF MEMS are a great source of problems
  - Interesting applications
  - Interesting physics (and not altogether understood)
  - Interesting numerical mathematics
- See also:
  - HiQLab: simulation of resonant MEMS
     www.cs.berkeley.edu/~dbindel/hiqlab/
  - Bindel and Govindjee. Elastic PMLs for resonator anchor loss simulations. *IJNME*, 64(6):789–818, October 2005.